Standard specifications of 100 mm Sn-doped β -Ga₂O₃ (001) substrate

Items		Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Resistivity (Ω·cm)		0.007-0.042	
Dimensions	Diameter (mm)	100 ±0.5	
	Orientation flat width (mm)	32.5 ±2.5	
	Index flat width (mm)	18.0 ±2.5	
	Thickness (mm)	0.65 ±0.02	
	Reference	Fig. 1	
Offset angle (degree)		[010]:0 ±1	
		[100]:0 ±1	
FWHM (arcsec)		[010]:50 or less	
		[100]:50 or less	
Surface	Front	СМР	
	Back	СМР	

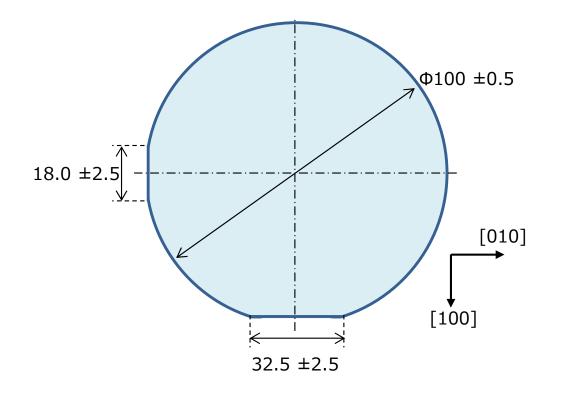


Fig. 1



Novel Crystal Technology, Inc.

Remarks

- 1 The edge exclusion width is 3 mm.
- 2 The opposite side of the OF may be chipped <18 mm, and the OF side <32.5 \pm 2.5 mm.
- 3 These products must be used for research and development purposes only.
- 4 The substrates must not be used as a seed crystal.
- 5 The specifications are subject to change without notice.

Standard specifications of 2 inch Sn-doped β-Ga₂O₃ (001) substrate

	Items	Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Resistivity (Ω·cm)		0.007-0.042	
Dimensions	Diameter (mm)	50.8 ±0.3	
	Orientation flat width (mm)	15.9 ±2.5	
	Index flat width (mm)	8.0 ±2.5	
	Thickness (mm)	0.65 ±0.02	
	Reference	Fig. 2	
Offset angle (degree)		[010]:0 ±1	
		[100]:0 ±1	
FWHM (arcsec)		[010]:50 or less	
		[100]:50 or less	
Surface	Front	СМР	
	Back	CMP	

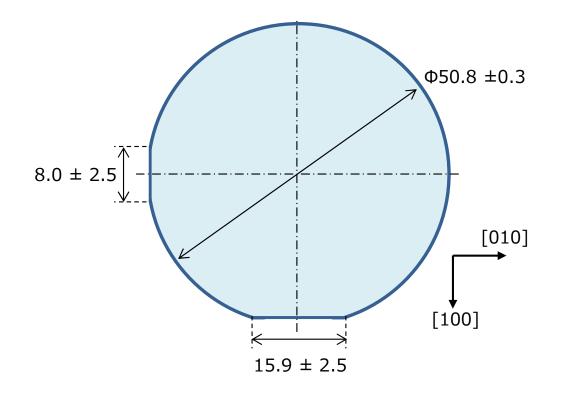


Fig.2



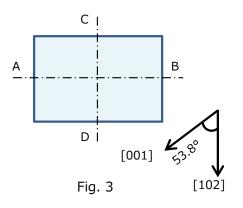
Novel Crystal Technology, Inc.

Remarks

- 1 The edge exclusion width is 3 mm.
- 2 The opposite side of the OF may be chipped < 8 mm, and the OF side $< 15.9 \pm 2.5$ mm.
- 3 These products must be used for research and development purposes only.
- 4 The substrates must not be used as a seed crystal.
- 5 The specifications are subject to change without notice.

Standard specifications of 10×15 mm² β-Ga₂O₃ (010) substrates

Items		Specifications			
Orientation		(010)			
Dopant		Sn	Undoped	Fe	
Conductivity		n-type	n-type	Insulating $(>10^{10}\Omega \cdot \text{cm})$	
Nd-Na (cm ⁻³)		1×10 ¹⁸ -9×10 ¹⁸	≦9×10 ¹⁷	-	
Dimensions	A-B (mm)	15 ±0.3	15 ±0.3	15 ±0.3	
	C-D (mm)	10 ±0.3	10 ±0.3	10 ±0.3	
	Thickness (mm)	0.5 ±0.02	0.5 ±0.02	0.5 ±0.02	
	Reference	Fig. 3	Fig. 3	Fig. 3	
Offset angle (degree)		⊥[102]:0 ±1	⊥[102]:0 ±1	⊥[102]:0 ±1	
		[102]:0 ±1	$[102]:0 \pm 1$	[102]:0 ±1	
FWHM (arcsec)		⊥[102]:150 or less	⊥[102]:150 or less	⊥[102]:150 or less	
		[102]:150 or less	[102]:150 or less	[102]:150 or less	
Surface	Front	CMP	CMP	CMP	
ace	Back	Grinding	Grinding	Grinding	



Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.

